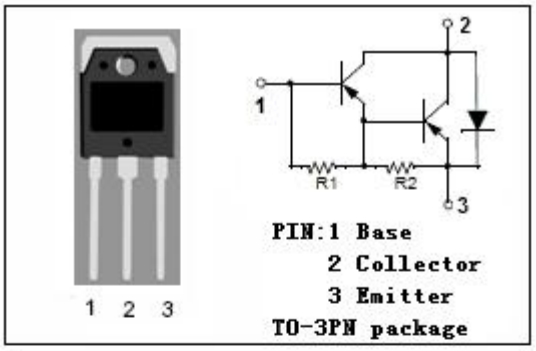
isc Silicon PNP Darlington Power Transistor 2SB897

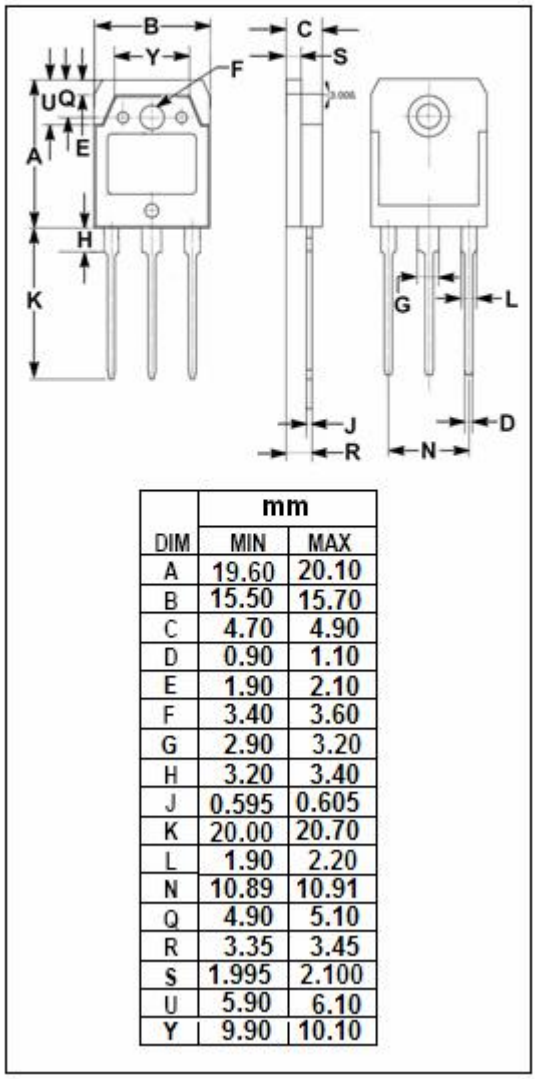
DESCRIPTION

- High DC Current Gain-
  : h_{FE} = 1000(Min)@ I_C= -10A
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$ = -1.5V(Max.) @I_C= 10A
- Complement to Type 2SD1210
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for audio frequency power amplifier and low speed high current switching industrial use.



DIM	mm MIN	mm MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-20	A
I_B	Base Current- Continuous	-1.0	A
P_C	Collector Power Dissipation @T_C=25℃	80	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA, I_B= 0	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -10A ,I_B= -25mA			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -10A ,I_B= -25mA			-2.0	V
I_{CBO}	Collector Cutoff current	V_{CB}= -100V, I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff current	V_{EB}= -8V, I_C= 0			-5	mA
h_{FE}	DC Current Gain	I_C= -10A ; V_{CE}= -2V	1000			